Amendments to the Claims:

1. (Currently Amended) A chip for a chip-containing portable article comprising:

   a monocrystaline silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

   an additional layer of monocrystaline silicon that:

   is ~~sealed~~ bonded to the active face of the monocrystaline silicon substrate layer by a ~~sealing~~ bonding layer;

   covers at least part of said active face; and

   comprises physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm.

2. (Withdrawn)

3. (Withdrawn)

4. (Cancelled)

5. (Previously Presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are silicon dopants.

6. (Previously Presented) A chip according to Claim 5, wherein the concentration of silicon dopants lies in the range 10^{17} to 10^{20} atoms per cm^3.

7. (Previously Presented) A chip according to Claim 5, wherein the silicon dopants are phosphorus or boron.

8. (Cancelled)

9. (Cancelled)

10. (Previously Presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by surface irregularities.

11. (Cancelled)

12. (Currently Amended) A chip according to claim 10, wherein the surfaces irregularities are provided in the face of the additional layer of monocrystaline silicon that is in contact with the ~~sealing~~ bonding layer.

13. (Currently Amended) A chip according to Claim 10, wherein the surface irregularities are provided in the face of the additional layer of montcrystaline silicon that is opposite to the face that is in contact with the ~~sealing~~ bonding layer.

14. (Currently Amended) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by at least one deposition of metal on the additional layer of moncrystaline silicon.

15. (Previously Presented) A chip according to Claim 14, wherein the metal deposition has a thickness greater than 50 Å.

16. (Currently Amended) A chip according to Claim 14, wherein the metal deposition is on the face of the additional of monocrystaline silicon that is in contact with the ~~sealing~~ bonding layer.

17. (Currently Amended) A chip according to Claim 14, wherein the metal deposition is on the face of the additional layer of monocrystaline silicon that is opposite to the face that is in contact with the ~~sealing~~ bonding layer.

18. (Cancelled)

19. (Previously Presented) A chip according to claim 16, wherein the metal deposition has a thickness of about 100 Å.

20. (Currently Amended) A portable article provided with a chip comprising:

a monocrystaline silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

an additional layer of moncrystaline silicon that:

is ~~sealed~~ bonded to the active face of the monocrystaline silicon substrate layer by a ~~sealing~~ bonding layer;

covers at least part of said active face; and

comprises physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm.

21. (currently amended) The chip according to Claim 5 wherein the silicon substrate layer comprises:

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm; and

wherein said physical means comprises silicon dopants in the face of the monocrystaline silicon substrate layer that is opposite to the active face.

22. (Currently Amended) The chip according to Claim 21, wherein the concentration of silicon dopants in the monocrystaline silicon substrate layer lies in the range 10^{17} to 10^{20} atoms per cm^3.

23. (Currently Amended) The chip according to Claim 22, wherein the silicon dopants in the monocrystaline silicon substrate layer are phosphorus or boron.

24. (Currently Amended) A chip according to Claim 10 wherein the monocrystaline silicon substrate layer comprises:

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm: and

wherein said physical means comprises surface irregularities in the face of the monocrystaline silicon substrate layer that is opposite to the active face.

25. (Currently Amended) A chip according to Claim 14 wherein the monocrystaline silicon substrate layer comprises:

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm; and

wherein said physical means comprising deposition of metal on the face of the monocrystaline silicon substrate layer that is opposite to the active face.

26. (Currently Amended) A chip for a chip-containing portable article comprising:

a monocrystaline silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm comprising silicon dopants in the face of the

monocrystaline silicon substrate layer that is opposite to the active face.

27. (Previously Presented) A chip according to Claim 26, wherein the concentration of silicon dopants lies in the range 10^{17} to 10^{20} atoms per cm^3.

28. (Previously Presented) A chip according to Claim 27, wherein the silicon dopants are phosphorus or boron.

29. (Currently Amended) A chip for a chip-containing portable article comprising:

a monocrystaline silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm comprising surface irregularities in the face of the monocrystaline silicon substrate layer that is opposite to the active face.

30. (Currently Amended) A chip for a chip-containing portable article comprising:

a monocrystaline silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

physical means for providing physical protection against the electromagnetic radiation in the infrared range at a wavelength longer than 1 μm comprising deposition of metal on the face of the monocrystaline silicon substrate layer that is opposite to the active face.

31. (Previously Presented) A chip according to Claim 30, wherein the metal deposition has a thickness greater than 50 Å.

32. (Previously Presented) A chip according to claim 30, wherein the metal deposition has a thickness of about 100 Å.